TO SEP. D TOP AND BOTTOM EDGES, SNAP—APART AN CARBON

FORM PTO-892 (REV. 3-78) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

NOTICE OF REFERENCES CITED

SERIAL NO.	GROUP ART UNIT	ATTACHMENT TO PAPER NUMBER
843454	114	2

APPLICANT(S): BLACHARD

U.S. PATENT DOCUMENTS

*		DOCUMENT NO.	DATE	NAME	CLASS	SUB-CLASS	FILING DATE IF APPROPRIATE
	A	4582565	4-86	KAWAKATSU	29	580	8-8-84
	B	4509249	4-85	GOTO ET AL.	29	576W	9-23-83
	C	4374455	2-83	GOODMAN	29	580	
	D	4546367	10-85	SCHUTTEN ET AL.	357	55	6-21-82
	E	4596999	6-86	GOBRECHT ET AL.	357	55	3-22-84
	F	4345265	8-82	BLACHARD	29	571	
	G						
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*		DOCUMENT NO.	DATE	COUNTRY	NAME	CLASS	SUB-CLASS	PERTINENT SHTS. DWG	PERTINENT PP. SPEC.
	L	0065447	4-84	JAPAN	KAZUYA	29	576W		
	M	0108325	6-84	JAPAN	TOSHIO	29	576W		
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EXAMINER	DATE
T. Thomas.	12-17-86.

*A copy of this reference is not being furnished with this office action.
(See Manual of Patent Examining Procedure, section 707.05 (a).)